

PATENT ASSIGNMENT

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SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT
CONVEYING PARTY DATA	
Name	Execution Date
DRAM MEMTECH LLC	02/01/2011
RECEIVING PARTY DATA	
Name:	DRAM MEMORY TECHNOLOGIES LLC
Street Address:	500 Newport Center Drive
City:	Newport Beach
State/Country:	CALIFORNIA
Postal Code:	92660
PROPERTY NUMBERS Total: 58	
Property Type	Number
Patent Number:	4980799
Patent Number:	5465063
Patent Number:	5691661
Patent Number:	5726950
Patent Number:	5751655
Patent Number:	5818768
Patent Number:	5905690
Patent Number:	5991232
Patent Number:	6049488
Patent Number:	6301187
Patent Number:	6310815
Patent Number:	6345348
Patent Number:	6359803
Patent Number:	6414881
Patent Number:	6452861

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PATENT
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Patent Number:	6515934
Patent Number:	6331962
Patent Number:	6570815
Patent Number:	6724686
Patent Number:	6522599
Patent Number:	6337832
Patent Number:	6765838
Patent Number:	5703831
Patent Number:	6014340
Patent Number:	6028805
Patent Number:	6396747
Patent Number:	6351423
Patent Number:	6205071
Patent Number:	5471430
Patent Number:	5267200
Patent Number:	5748560
Patent Number:	5253211
Patent Number:	5511029
Patent Number:	5587950
Patent Number:	5909141
Patent Number:	5434742
Patent Number:	5745336
Patent Number:	5404335
Patent Number:	5610871
Patent Number:	5973983
Patent Number:	RE36932
Patent Number:	5673232
Patent Number:	5629897
Patent Number:	5708611
Patent Number:	5764590
Patent Number:	5936459
Application Number:	08688077
Patent Number:	5910927
Patent Number:	5982705
Patent Number:	5963902

Patent Number:	6078542
Patent Number:	6377512
Patent Number:	6166989
Patent Number:	6246614
Patent Number:	6587385
Patent Number:	6426908
Patent Number:	6487136
Patent Number:	6327208

CORRESPONDENCE DATA

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NAME OF SUBMITTER:

Clay McGurk

Total Attachments: 6

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ASSIGNMENT

WHEREAS, DRAM MEMTECH LLC, a Texas limited liability company having a place of business at 6136 Frisco Square Blvd., Suite 385, Frisco, Texas 75034 USA (hereafter, together with any successors, legal representatives or assigns thereof, called "Assignor") is the owner of the entire right, title, and interest and assignee of the **U.S. Patent Nos. listed on Exhibit A attached hereto;**

AND WHEREAS, DRAM MEMORY TECHNOLOGIES LLC, a California limited liability company having a place of business at 500 Newport Center Drive, Newport Beach, CA 92660 USA (hereafter, together with any successors, legal representatives or assigns thereof, called "ASSIGNEE") wants to acquire the entire right, title and interest in and to said **U.S. Patent Nos. listed on Exhibit A attached hereto**, and all the inventions therein, and Assignor is willing to enter into such assignment.

NOW, THEREFORE, in consideration of the sum of One Dollar (\$1.00) in hand paid and other good and valuable consideration the receipt of which from ASSIGNEE is hereby acknowledged, Assignor has sold, assigned, transferred and set over, and does hereby sell, assign, transfer and set over to ASSIGNEE the entire right, title and interest in and to the **U.S. Patent Nos. listed on Exhibit A attached hereto**, and all continuations, divisionals, reexaminations, reissues and substitutes thereof, all inventions therein, including without limitation all rights to claim priority on the basis thereof, and any and all applications for patents which are or may hereafter be filed for this invention in any foreign country and all patents which may be granted on these inventions in any foreign country, and all extensions, renewals, and reissues thereof, and including without limitation, all rights to sue for past, present and future infringement, including the right to collect and receive any damages, royalties, or settlements for such infringements, all rights to sue for injunctive or other equitable relief, and any and all causes of action relating to any of the inventions or discoveries thereof;

Assignor hereby covenants that it has full right to convey the entire interest herein assigned, and that it has not executed, and will not execute, any agreement in conflict with this Assignment;

Assignor hereby further covenants and agrees that it will communicate to ASSIGNEE any and all facts known to it respecting said patents, and testify in any legal proceeding, sign all lawful papers, execute and deliver all papers and take any actions that may be necessary or desirable to perfect the title to any aforementioned patents and inventions, execute all divisional, continuation, reexamination, reissue and substitute applications, and make all rightful oaths and generally do everything possible to aid ASSIGNEE to obtain and enforce proper patent protection for said inventions in all countries.

IN TESTIMONY WHEREOF, I hereunto set my hand this 1st day of February, 2011.

DRAM MEMTECH LLC
(Assignor)

By 
Name Dooyong Lee
Title CEO

EXHIBIT A**U.S. PATENTS & APPLICATIONS**

US Patent No.	US Application No.	Filing Date	Issue Date	Title
4980799	7459998	1/4/1990	12/25/1990	ELECTROSTATIC CDRAMITY DEVICE IN SEMICONDUCTOR MEMORY DEVICE, AND APPARATUS FOR AND METHOD OF DRIVING SENSE AMPLIFIER USING ELECTROSTATIC CDRAMITY DEVICE
5465063	8049398	4/21/1993	11/7/1995	PULSE GENERATING CIRCUIT WITH TEMPERATURE COMPENSATION
5691661	8458775	6/2/1995	11/25/1997	PULSE GENERATING CIRCUIT AND A SEMICONDUCTOR MEMORY DEVICE PROVIDED WITH THE SAME
5726950	8779829	1/7/1997	3/10/1998	SYNCHRONOUS SEMICONDUCTOR MEMORY DEVICE PERFORMING INPUT/OUTPUT OF DATA IN A CYCLE SHORTER THAN AN EXTERNAL CLOCK SIGNAL CYCLE
5751655	8788803	1/23/1997	5/12/1998	A SYNCHRONOUS TYPE SEMICONDUCTOR MEMORY DEVICE HAVING INTERNAL OPERATION TIMINGS DETERMINED BY COUNT VALUES OF AN INTERNAL COUNTER
5818768	8767496	12/16/1996	10/6/1998	OPERATION MODE SETTING CIRCUIT IN SEMICONDUCTOR DEVICE
5905690	9058987	4/13/1998	5/18/1999	SYNCHRONOUS SEMICONDUCTOR DEVICE HAVING CIRCUITRY CAPABLE OF SURELY RESETTING TEST MODE
5991232	9143253	8/28/1998	11/23/1999	CLOCK SYNCHRONOUS MEMORY EMBEDDED SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE
6049488	9122762	7/27/1998	4/11/2000	CLOCK SYNCHRONOUS SEMICONDUCTOR MEMORY DEVICE CAPABLE OF PREVENTING OUTPUTTING OF INVALID DATA
6301187	9226064	1/6/1999	10/9/2001	SYNCHRONOUS TYPE SEMICONDUCTOR MEMORY DEVICE PERMITTING REDUCTION IN RATIO OF AREA OCCUPIED BY CONTROL CIRCUIT IN CHIP AREA
6310815	9131346	8/7/1998	10/30/2001	MULTI-BANK SEMICONDUCTOR MEMORY DEVICE SUITABLE FOR INTEGRATION WITH LOGIC
6345348	8798950	2/11/1997	2/5/2002	MEMORY SYSTEM CAPABLE OF SUPPORTING DIFFERENT MEMORY DEVICES AND A MEMORY DEVICE USED THEREFOR
6359803	9759319	1/16/2001	3/19/2002	Semiconductor memory device that can access two regions alternately at high speed

6414881	9876078	6/8/2001	7/2/2002	SEMICONDUCTOR DEVICE CAPABLE OF GENERATING INTERNAL VOLTAGE EFFECTIVELY
6452861	9981811	10/19/2001	9/17/2002	SEMICONDUCTOR MEMORY DEVICE ALLOWING SIMULTANEOUS INPUTTING OF N DATA SIGNALS
6515934	9986973	11/13/2001	2/4/2003	SEMICONDUCTOR DEVICE INCLUDING INTERNAL POTENTIAL GENERATING CIRCUIT ALLOWING TUNING IN SHORT PERIOD OF TIME AND REDUCTION OF CHIP AREA
6331962	9489474	1/21/2000	12/18/2001	Semiconductor device including voltage down converter allowing tuning in short period of time and reduction of chip area
6570815	9973886	10/11/2001	5/27/2003	SEMICONDUCTOR MEMORY DEVICE CAPABLE OF ADJUSTING PHASE OF OUTPUT DATA AND MEMORY SYSTEM USING THE SAME
6724686	10339288	1/10/2003	4/20/2004	OPERABLE SYNCHRONOUS SEMICONDUCTOR MEMORY DEVICE SWITCHING BETWEEN SINGLE DATA RATE MODE AND DOUBLE DATA RATE MODE
6522599	10025857	12/26/2001	2/18/2003	OPERABLE SYNCHRONOUS SEMICONDUCTOR MEMORY DEVICE SWITCHING BETWEEN SINGLE DATA RATE MODE AND DOUBLE DATA RATE MODE
6337832	9272194	3/18/1999	1/8/2002	OPERABLE SYNCHRONOUS SEMICONDUCTOR MEMORY DEVICE SWITCHING BETWEEN SINGLE DATA RATE MODE AND DOUBLE DATA RATE MODE
6765838	10209901	8/2/2002	7/20/2004	REFRESH CONTROL CIRCUITRY FOR REFRESHING STORAGE DATA

5703831	08/768081	12/16/1996	12/30/1997	SYNCHRONOUS SEMICONDUCTOR MEMORY DEVICE HAVING INTERNAL CIRCUITRY ENABLED ONLY WHEN COMMANDS ARE APPLIED IN NORMAL SEQUENCE
6014340	08/978440	11/25/1997	1/11/2000	SYNCHRONOUS SEMICONDUCTOR MEMORY DEVICE HAVING INTERNAL CIRCUITRY ENABLED ONLY WHEN COMMANDS ARE APPLIED IN NORMAL SEQUENCE
6028805	09/186895	11/6/1998	2/22/2000	VOLATILE MEMORY AND EMBEDDED DYNAMIC RANDOM ACCESS MEMORY
6396747	09/461093	12/14/1999	5/28/2002	SEMICONDUCTOR MEMORY DEVICE CAPABLE OF HIGH SPEED INPUT/OUTPUT OF WIDE BANDWIDTH DATA BY IMPROVING USAGE EFFICIENCY OF EXTERNAL DATA BUS

6351423	09/768061	1/24/2001	2/26/2002	Semiconductor memory device including sense amplifier circuit differing in drivability between data write mode and data read mode
6205071	09/339389	6/24/1999	3/20/2001	SEMICONDUCTOR MEMORY DEVICE INCLUDING SENSE AMPLIFIER CIRCUIT DIFFERING IN DRIVABILITY BETWEEN DATA WRITE MODE AND DATA READ MODE
5471430	08/245784	5/19/1994	11/28/1995	TEST CIRCUIT FOR REFRESH COUNTER OF CLOCK SYNCHRONOUS TYPE SEMICONDUCTOR MEMORY DEVICE
5267200	07/399946	8/31/1989	11/30/1993	SEMICONDUCTOR MEMORY DEVICE AND OPERATING METHOD THEREOF WITH TRANSFER TRANSISTOR USED AS A MEMORY HOLDING MEANS
5748560	08/740175	10/28/1996	5/5/1998	SYNCHRONOUS SEMICONDUCTOR MEMORY DEVICE WITH AUTO PRECHARGE OPERATION EASILY CONTROLLED
5253211	07/866048	4/9/1992	10/12/1993	SEMICONDUCTOR MEMORY DEVICE CAPABLE OF PERFORMING REFRESH OPERATION IN READING OR WRITING
5511029	08/246582	5/19/1994	4/23/1996	TEST CIRCUIT IN CLOCK SYNCHRONOUS SEMICONDUCTOR MEMORY DEVICE
5587950	08/461907	6/5/1995	12/24/1996	TEST CIRCUIT IN CLOCK SYNCHRONOUS SEMICONDUCTOR MEMORY DEVICE
5909141	08/874351	6/13/1997	6/1/1999	STEP-UP POTENTIAL SUPPLY CIRCUIT AND SEMICONDUCTOR STORAGE DEVICE
5434742	07/995977	12/23/1992	7/18/1995	CAPACITOR FOR SEMICONDUCTOR INTEGRATED CIRCUIT AND METHOD OF MANUFACTURING THE SAME
5745336	08/417839	4/6/1995	4/28/1998	CAPACITOR FOR SEMICONDUCTOR INTEGRATED CIRCUIT
5404335	08/039661	3/30/1993	4/4/1995	DYNAMIC TYPE SEMICONDUCTOR MEMORY DEVICE OPERABLE IN A SELF-REFRESHING MODE
5610871	08/341145	11/16/1994	3/11/1997	SEMICONDUCTOR MEMORY DEVICE HAVING A HIERARCHICAL BIT LINE STRUCTURE WITH REDUCED INTERFERENCE NOISE
5973983	08/786386	1/16/1997	10/26/1999	SEMICONDUCTOR MEMORY DEVICE HAVING A HIERARCHICAL BIT LINE STRUCTURE WITH REDUCED INTERFERENCE NOISE
Re. 36932	09/221835	12/28/1998	10/31/2000	SEMICONDUCTOR MEMORY DEVICE OPERATING STABLY UNDER LOW POWER SUPPLY VOLTAGE WITH LOW POWER CONSUMPTION
5673232	08/486755	6/6/1995	09/30/1997	SEMICONDUCTOR MEMORY DEVICE OPERATING STABLY UNDER LOW POWER SUPPLY VOLTAGE WITH LOW POWER CONSUMPTION

5629897	08/524927	9/8/1995	5/13/1997	A SYNCHRONOUS SEMICONDUCTOR MEMORY DEVICE HAVING A MODE REQUIRING AN INTERNAL CLOCK SIGNAL AND A MODE NOT REQUIRING THE INTERNAL CLOCK SIGNAL
5708611	08/801889	2/18/1997	1/13/1998	SYNCHRONOUS SEMICONDUCTOR MEMORY DEVICE
5764590	08/735149	10/22/1996	6/9/1998	SYNCHRONOUS SEMICONDUCTOR MEMORY DEVICE WHICH ALLOWS SWITCHING OF BIT CONFIGURATION
5936459	08/942485	10/2/1997	8/10/1999	INTERNAL POTENTIAL GENERATING CIRCUIT AND BOOSTED POTENTIAL GENERATING UNIT USING PUMPING OPERATION
-	*08/688077	7/29/1996	-	INTERNAL POTENTIAL GENERATING CIRCUIT AND BOOSTED POTENTIAL GENERATING UNIT USING PUMPING OPERATION
5910927	08/931525	9/16/1997	6/8/1999	MEMORY DEVICE AND SENSE AMPLIFIER CONTROL DEVICE
5982705	09/045834	3/23/1998	11/9/1999	SEMICONDUCTOR MEMORY DEVICE PERMITTING LARGE OUTPUT CURRENT FROM OUTPUT BUFFER
5963902	08/903477	7/30/1997	10/5/1999	METHODS AND APPARATUS FOR DECREASING THE SIZE OF GENERATED MODELS TRAINED FOR AUTOMATIC PATTERN RECOGNITION
6078542	09/204282	12/3/1998	6/20/2000	SEMICONDUCTOR MEMORY DEVICE IMPLEMENTING MULTI-BANK CONFIGURATION WITH REDUCED NUMBER OF SIGNAL LINES
6377512	09/666133	9/20/2000	4/23/2002	CLOCK SYNCHRONOUS TYPE SEMICONDUCTOR MEMORY DEVICE THAT CAN SWITCH WORD CONFIGURATION
6166989	09/261133	3/3/1999	12/26/2000	CLOCK SYNCHRONOUS TYPE SEMICONDUCTOR MEMORY DEVICE THAT CAN SWITCH WORD CONFIGURATION
6246614	09/467914	12/21/1999	6/12/2001	CLOCK SYNCHRONOUS SEMICONDUCTOR MEMORY DEVICE HAVING A REDUCED ACCESS TIME
6587385	09/843689	4/30/2001	7/1/2003	CLOCK SYNCHRONOUS SEMICONDUCTOR MEMORY DEVICE HAVING A REDUCED ACCESS TIME
6426908	09/511927	2/23/2000	7/30/2002	SEMICONDUCTOR MEMORY DEVICE WITH REDUCED CURRENT CONSUMPTION IN DATA HOLD MODE
6487136	10/115618	4/4/2002	11/26/2002	SEMICONDUCTOR MEMORY DEVICE WITH REDUCED CURRENT CONSUMPTION IN DATA HOLD MODE
6327208	09/645610	8/25/2000	12/4/2001	Semiconductor memory device having self refresh mode